

FORM PTO-1449 (Modified) LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	Attorney Docket No.: AM1084D01/T9320 TTC No.: 016301-009320US Applicant: David Cheung et al. Filing Date: October 15, 1999	Application No.: 09/418,818 Group: Unknown
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Reference Designation	U.S. PATENT DOCUMENTS	Page 1
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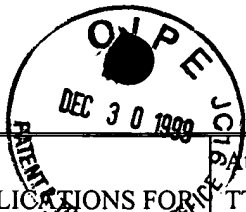
Examiner Initial	Document No.	Date	Name	Class	Sub-class	Filing Date (If Appropriate)
AA	5,665,214	09/1997	Iturralde	204	298.03	
AB	5,436,463	07/25/95	Rostoker	250	559.04	
AC	5,330,883	07/19/94	Garza	430	513	
AD	5,340,621	08/23/94	Matsumoto et al.	427	571	
AE	5,288,527	02/22/94	Jousse et al.	427	579	
AF	5,246,744	09/21/93	Matsuda et al.	427	574	
AG	5,178,905	01/12/93	Kanai et al.	427	570	
AH	5,068,124	11/26/91	Batey et al.	427	39	
AI	4,992,306	02/12/91	Hochberg et al	427	255.3	
AJ	4,992,299	02/12/91	Hochberg et al.	427	38	
AK	4,910,122	03/20/90	Arnold et al.	430	313	
AL	4,888,190	12/1989	Felts et al.	427	10	
AM	4,877,641	10/31/89	Dory	427	38	
AN	3,990,100	11/02/76	Mamine et al.	357	30	

FOREIGN PATENT DOCUMENTS

	Document No.	Date	Country	Class	Sub-class	Translation (Yes/No)
AO	06-240459	Aug. 1994	Japan (abstract only)			yes
AP	0 588 087 A2	Mar. 1994	EPO			yes
AQ	01-187239	July 1989	Japan (abstract only)			yes
AR	0 291 181 A2	11/17/88	Europe	H01J	37/32	

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)
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AS	Database CAPLUS, Chemical Abstracts, Vol. 120 (Columbus, OH), Abstract No. 121821 issued 1994, Kushner, Mark J., "Plasma Chemistry of Helium/Oxygen/Silane and Helium/Nitrous Oxide/Silane Mixtures for Remote Plasma-Activated Chemical Vapor Deposition of Silicon Dioxide", Journal of Applied Physics (1993, 74(11) 6538-53) 1994.
AT	Ogawa, T. et al., "SiOxNy:H: High Performance Anti-Reflective Layer for the Current and Future Optical Lithography", SPIE (1994), 2197:722-732.
AU	Database CAPLUS, Chemical Abstracts, Vol. 119 (Columbus, OH), Abstract No. 60911 issued 1993, Smith et al., "Chemistry of Silicon Dioxide Plasma Deposition", Journal of the Electrochemical Society, 140(5), 1496-503, 1993.
AV	Hishikawa et al., "Principles for Controlling the Optical and Electrical Properties of Hydrogenated Amorphous Silicon Deposited from a Silane Plasma", Journal of Applied Physics, 73 990, 4227-42.31, May 1993.
AW	Database CAPLUS, Chemical Abstracts, Vol. 111 (Columbus, OH) Abstract No. 145111 issued 1989, Rahman, Saadah Abdul, "The Effect of Helium Dilution n PECVD Silicon Dioxide", Jurnal Fizik Malaysia, 10(1), 20-3, 1989.
AX	Knolle, "Correlation of Refractive Index and Silicon Content of Silicon Oxynitride Films", Thin Solid Films, 168:123-132, Jan. 1989.



FORM PTO-1449 (Modified) LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (page 2)	Attorney Docket No.: AM1084D01/T9320	Application No.: 09/418,818
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	Applicant: David Cheung et al.	
	Filing Date: October 15, 1999	Group: Unknown

OTHER ART (continued)

<input checked="" type="checkbox"/> AY	Tsu, et al., "Deposition of Silicon Oxynitride Thin Films by Remote Plasma Enhanced Chemical Vapor Deposition", <i>Journal of Vacuum Science & Technology, Part A</i> , 5(4): 1998-2000, July/Aug. 1987.
<input type="checkbox"/> AZ	Database CAPLUS, Chemical Abstracts, Vol. 105 (Columbus, OH) Abstract No. 49711 issued 1986, Pai et al., "Infrared Spectroscopic Study of Silicon Oxide (SiO _x). Films Produced by Plasma Enhanced Chemical Vapor Deposition", <i>Journal of Vacuum Science and Technology</i> , 4(3, Pt. 1), 689-94, 1986.
<input type="checkbox"/> AAA	Tsu et al., "Local Atomic Structure in thin Films of Silicon Nitride and Silicon Diimide Produced by Remote Plasma-Enhanced Chemical-Vapor Deposition", <i>Physical Review B : Condensed Matter</i> , Vol. 33, No. 10, American Physical Society, pp. 7069-7076, May 1986.
EXAMINER	DATE CONSIDERED

Paul J. J... *5/7/01*

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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